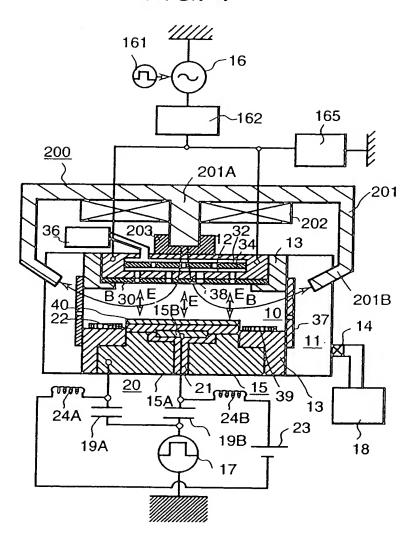
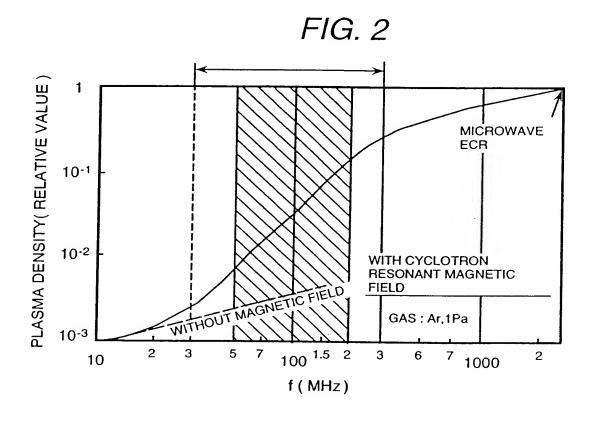
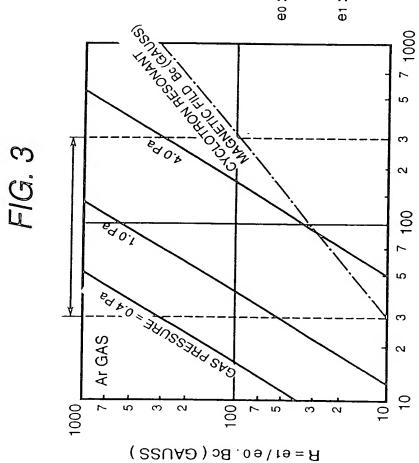
FIG. 1









Bc =  $2\pi f \cdot \frac{m}{e}$ 

eo : ENERGY OBTAINED BY ELCTRON DURING ONE CYCLE OF RF UNDER CONDITION WITHOUT MAGNETIC FIELD e1: ENERGY OBTAINED BY ELCTRON DURING ONE CYCLE OF RF UNDER CONDITION APPLIED WITH CYCLOTRON RESONANT MAGNETIC FIELD

f(MHz)



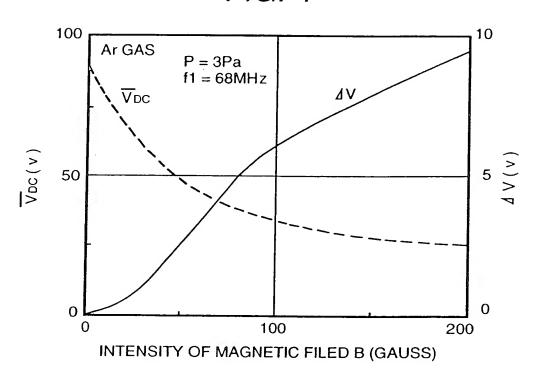
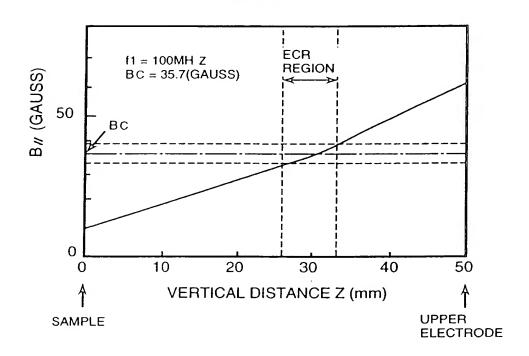
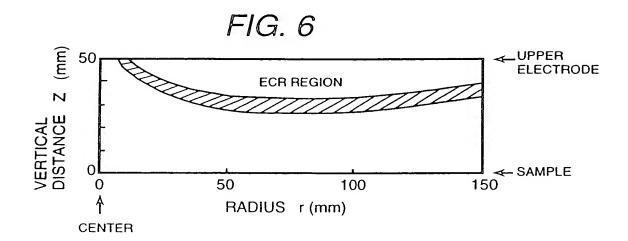
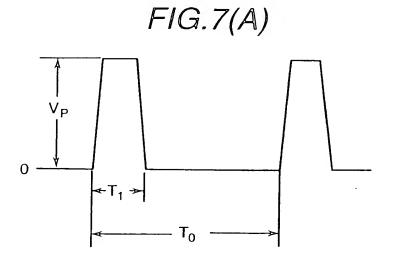
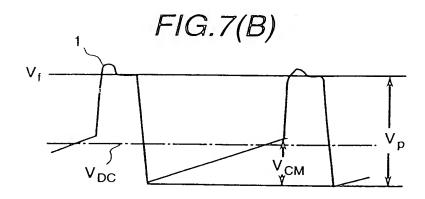


FIG. 5





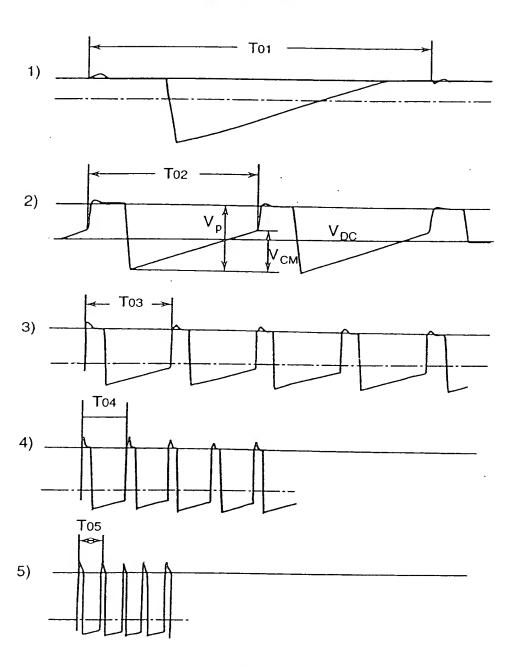




$$V_{CM} = \frac{q}{c} = \frac{i_i \cdot (T_0 - T_1)}{(\epsilon_{\gamma} \epsilon_0 / d) \times K}$$

- $i_i$ : ION CURRENT DENSITY
- $\epsilon_{-\gamma}$  : SPECIFIC DIELECTRIC CONSTANT OF ELECTROSTATIC ATTRACTING FILM
  - d : THICKNESS OF ELECTROSTATIC ATTRACTING FILM
  - K : ELECTRODE COVERING RATIO OF ELECTROSTATIC ATTRACTING FILM

FIG. 8



To1: To2: To3: To4: To5 = 16:8:4:2:1

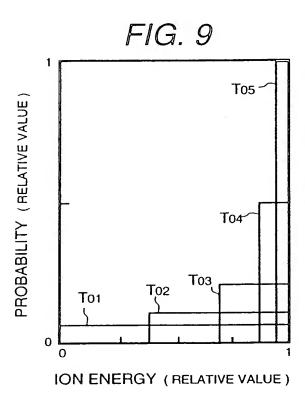
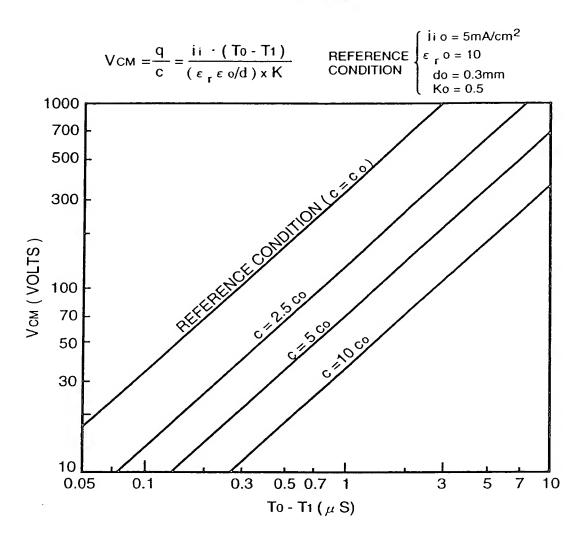


FIG. 10



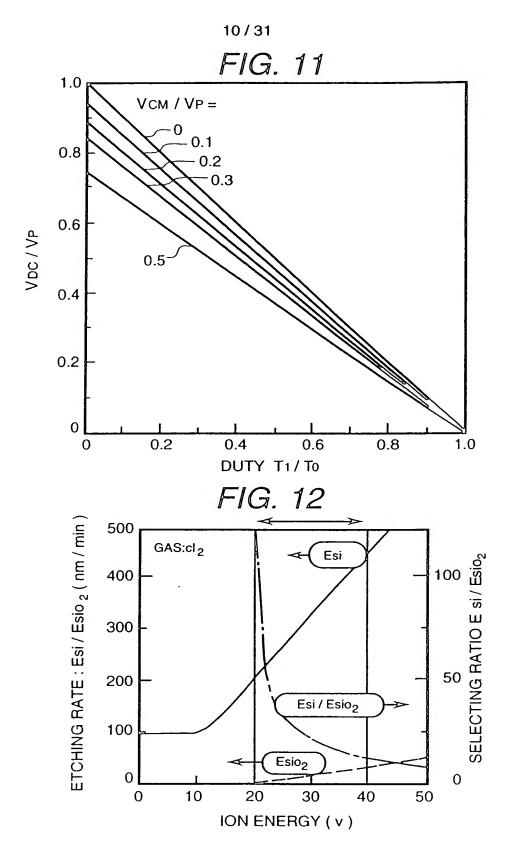


FIG. 13 GAS:CF 4 ETCHING RATE : Esi / Esio  $_2$  ( nm / min ) 100 600 SELECTING RATIO E si / Esio<sub>2</sub> 400 Esio<sub>2</sub> / Esi Esio<sub>2</sub> 50 200 Esi 0 -200 200 0 400 600 800 1000 ION ENERGY (v)

FIG. 14

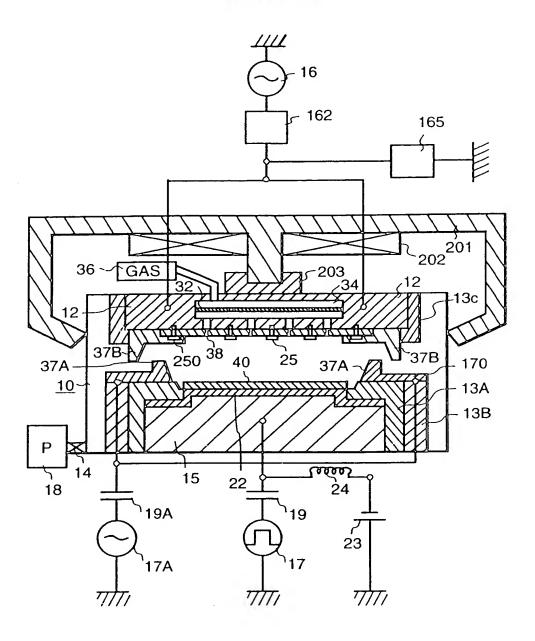


FIG. 15

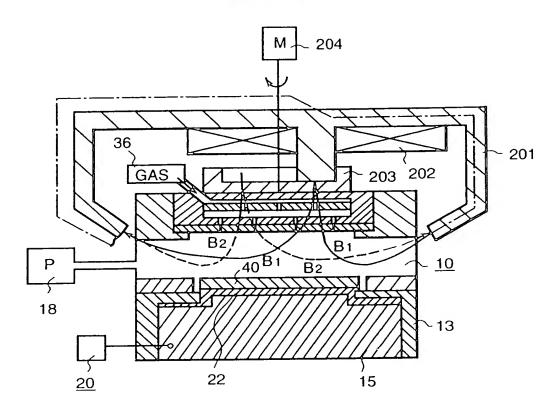
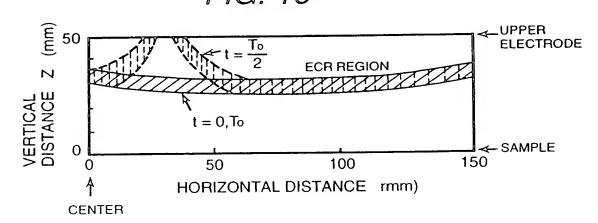


FIG. 16







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FIG. 17

RANGE OF SAMPLE

O

X

FIG. 18

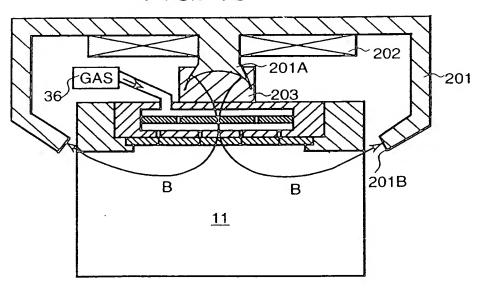


FIG. 19

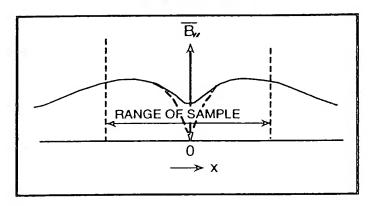
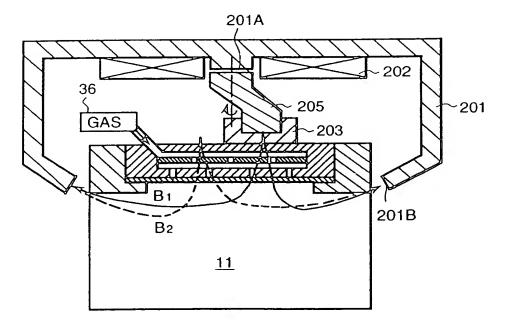
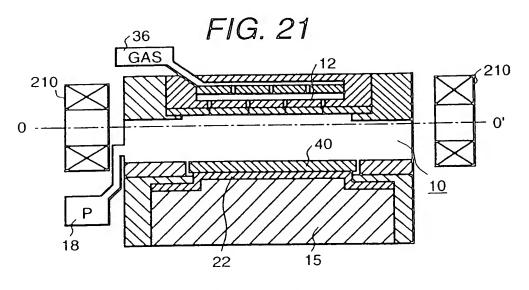


FIG. 20







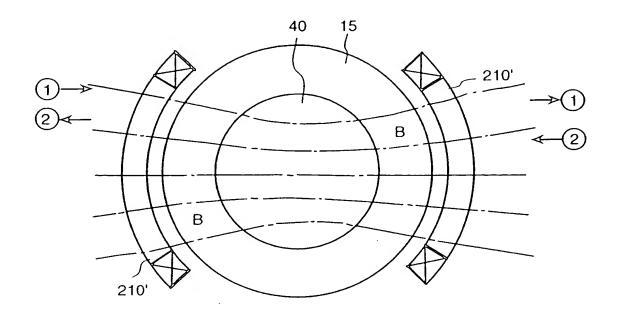
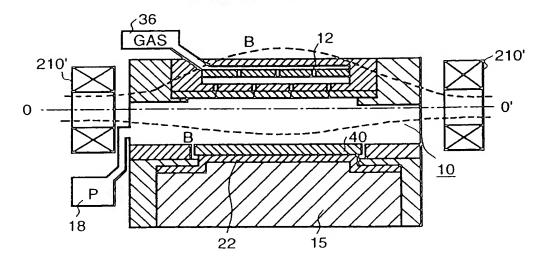


FIG. 24



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FIG. 25

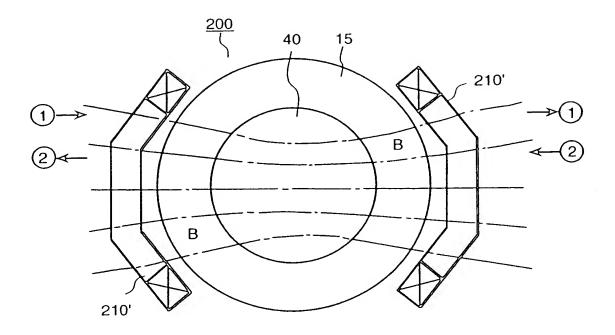


FIG. 26

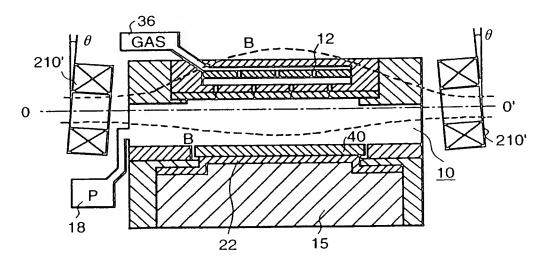


FIG. 27

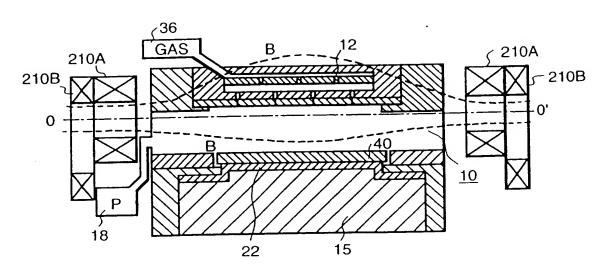


FIG. 28

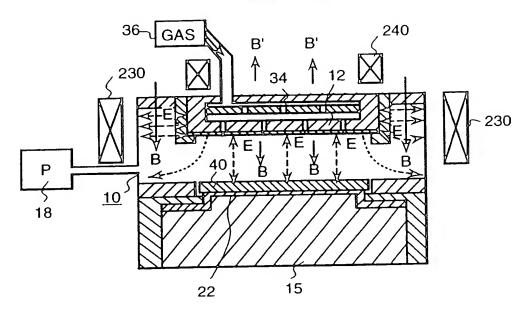


FIG. 29

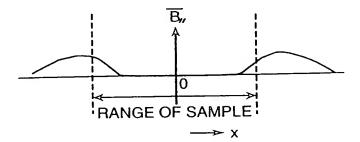


FIG. 30

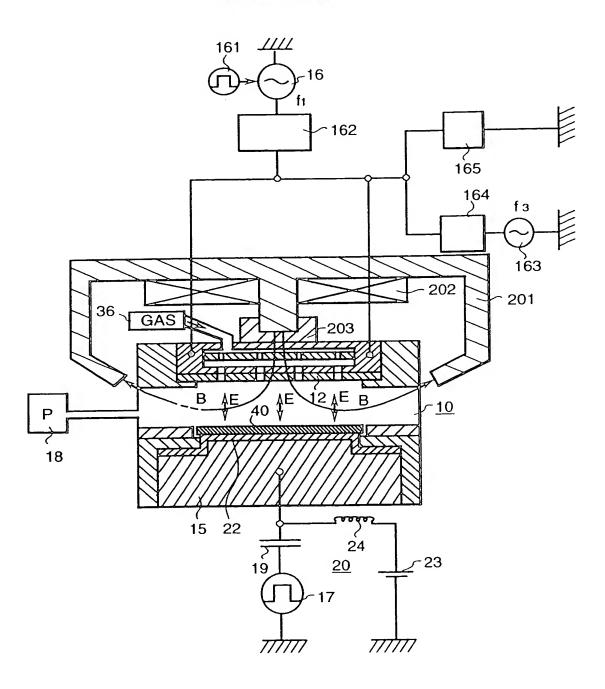


FIG. 31

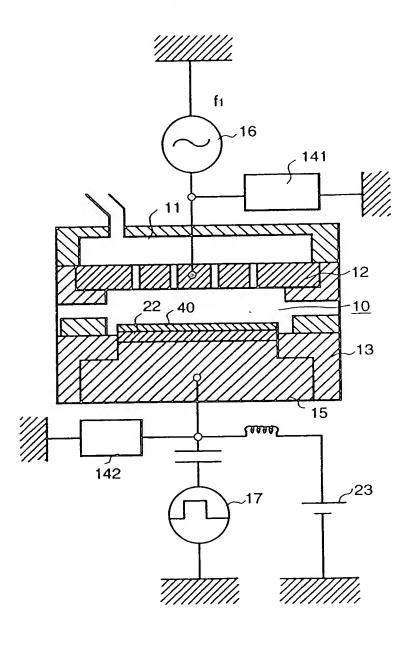
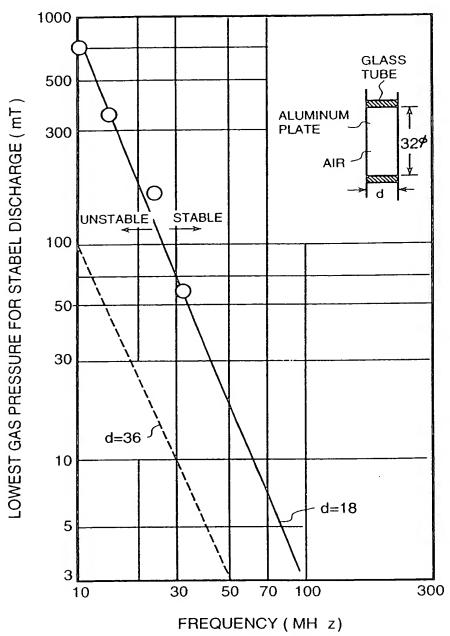
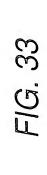


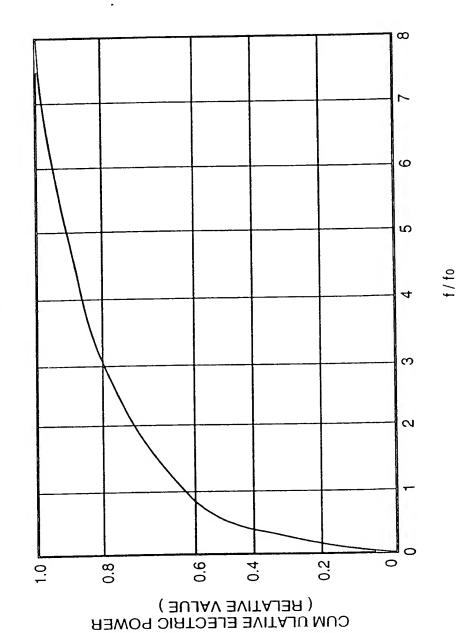


FIG. 32

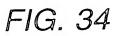


FREQUENCY-LOWEST GAS PRESSURE FOR STABLE DISCHARGE CHARACTERISTC





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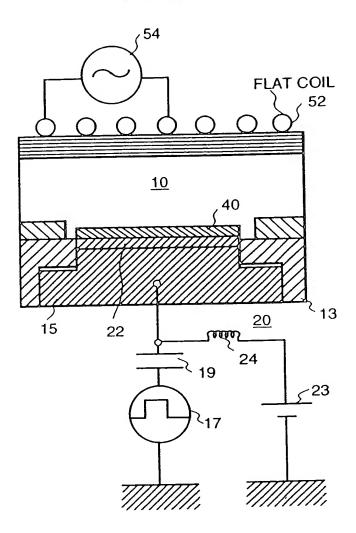
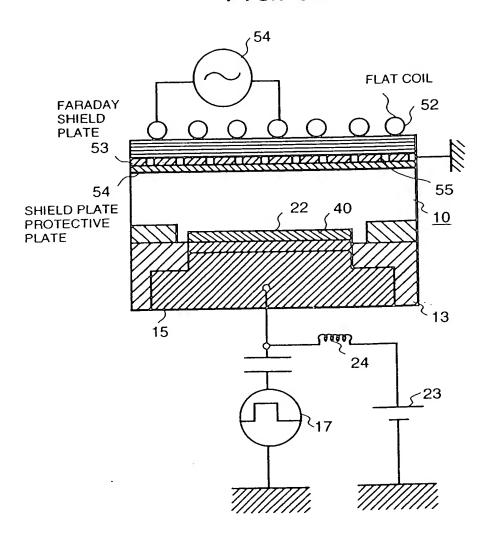


FIG. 35

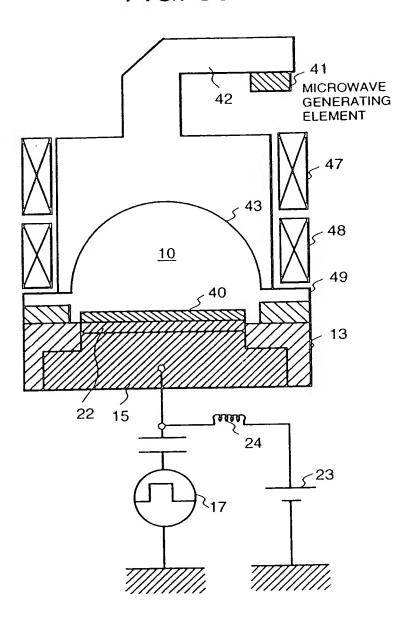






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FIG. 36

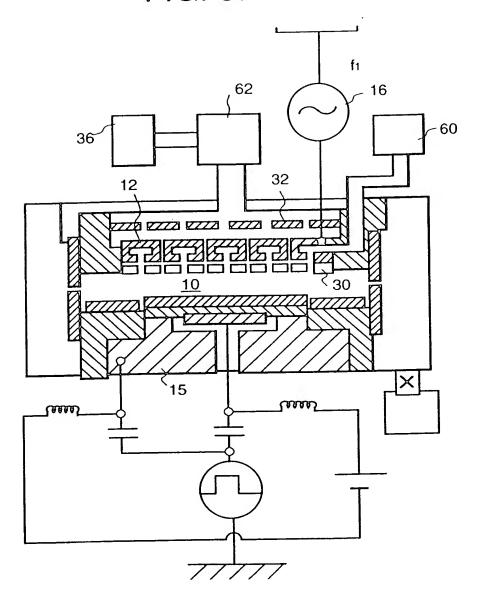






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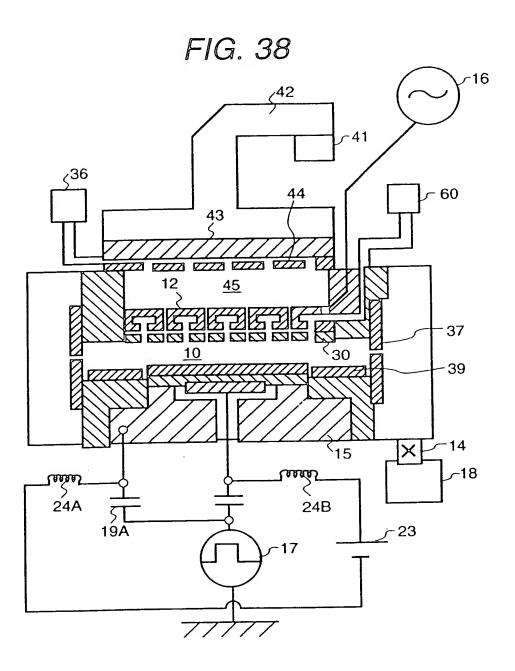
FIG. 37







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FIG. 39

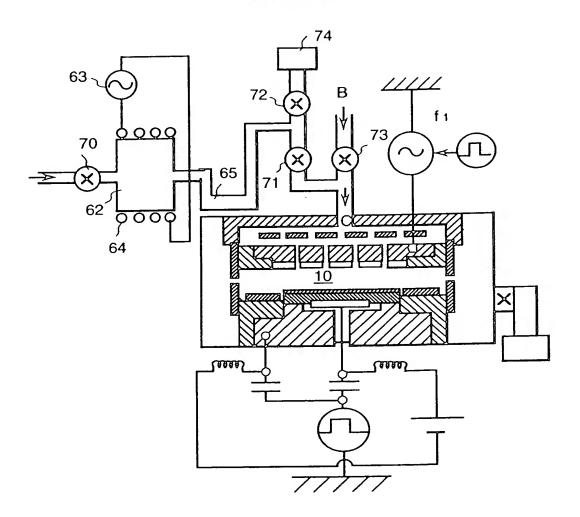


FIG. 40

